

PowerTech

POWERTECH INC

90 AMPERES

PT-7511

T-33-15

SILICON NPN TRANSISTOR**MAXIMUM RATINGS**

	SYMBOL	PT-7511
Collector-Base Voltage	V_{CBO}	200V
Collector-Emitter Voltage	V_{CEO}	200V
Emitter-Base Voltage	V_{EBO}	10V
Peak Collector Current	I_{CM}^*	90A
D.C. Collector Current	I_C	50A
Power Dissipation at 25°C Case Temperature	P_D	350W
Power Dissipation at 100°C Case Temperature	P_D	200W
Operating Junction Temperature Range	T_J	-65 to 200°C
Storage Temperature Range	T_A	-65 to 200°C
Thermal Resistance	θ_{JC}	0.5° C/W
Package		TO-63

ELECTRICAL CHARACTERISTICS (at 25°C unless noted)

TEST	SYMBOL	LIMITS		UNIT	TEST CONDITIONS
		PT-7511			
		MIN.	MAX.		
D.C. Current Gain*	h_{FE}	10	40		$I_C=50A, V_{CE}=2V$
D.C. Current Gain*	h_{FE}	5	—		$I_C=90A, V_{CE}=4V$
Collector Saturation Voltage*	$V_{CE(sat)}$	—	0.6	V	$I_C=50A, I_B=6A$
Collector Saturation Voltage*	$V_{CE(sat)}$	—	1.5	V	$I_C=90A, I_B=20A$
Base Emitter Voltage*	V_{BE}	—	1.5	V	$I_C=50A, V_{CE}=2V$
Base Emitter Voltage*	V_{BE}	—	2.5	V	$I_C=90A, V_{CE}=4V$
Collector-Emitter Breakdown Voltage*	$V_{CEO(sus)}$	200	—	V	$I_C=200mA, I_B=0$
Collector Cut-off Current	I_{CBO}	—	2.0	mA	$V_{CB}=200V, I_{EB}=0$
Collector Cut-off Current @ 150°C	I_{CBO}	—	10	mA	$V_{CB}=100V, I_{EB}=0$
Emitter Cut-off Current	I_{EBO}	—	1.0	mA	$V_{EB}=8V, I_{CB}=0$
Gain Bandwidth Product Typ.	f_t	1.0	—	MHz	$I_C=5A, V_{CE}=10V$ $f=100KHz$
Collector Capacitance	C_{obo}	—	1800	pf	$V_{CB}=10V$
Switching Speed Typ.	t_r	—	2.5	μs.	
(PowerTech Test Circuit)	t_s	—	3	μs.	$I_C=50A$
	t_f	—	2.5	μs.	$I_{B1}=5A, I_{B2}=10A$

*PW ≤ 300μs., D.C. ≤ 2%